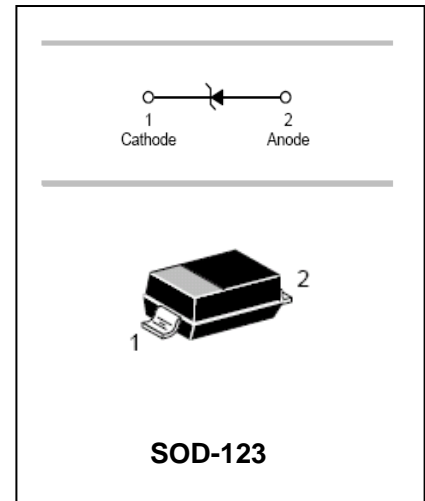


FEATURES

- Miniaturized package size for high density applications
- 5% high precision regulated voltage stability
- High reliability chip and packaging process

APPLICATIONS

- Mobile phone
- Portable device
- High precision computer motherboard



ORDERING INFORMATION

Type No.	Marking	Package Code
BZT52C2V0-BZT52C75	See Page2-3	SOD-123

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Forward Voltage @ I _F =10mA	V _F	0.85	V
Power Dissipation ^①	P _d	500	mW
Thermal resistance, junction to ambient air ^①	R _{θjA}	556	°C/W
Thermal resistance, junction to ambient air ^②	R _{θjA}	417	°C/W
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55~150	°C

Notes: 1. FR-5=1.0x0.75x0.62 in.

2. Alumina=0.4x0.3x0.024 in.,99.5% alumina

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

DEVICE	Marking	VZ(V) @ IZ=5mA			ZZ@ IZ1=1mA	ZZ @ IZ2 = 5 mA	ZZ @ IZ3 = 20mA	IR@VR	VR	Typical Temperature Coefficient(mV/°C)@ IZ=5mA	
		MIN	NOM	MAX	(Ω)	(Ω)	(Ω)	(uA)	V	Min	Max
BZT52C2V4	WX	2.28	2.4	2.52	570	95	47.5	40	1	-3.5	0
BZT52C2V7	W1	2.57	2.7	2.84	570	95	47.5	16	1	-3.5	0
BZT52C3V0	W2	2.85	3	3.15	570	90	47.5	8	1	-3.5	0
BZT52C3V3	W3	3.14	3.3	3.47	570	90	38	4	1	-3.5	0
BZT52C3V6	W4	3.42	3.6	3.78	570	85	38	4	1	-3.5	0
BZT52C3V9	W5	3.72	3.9	4.08	570	85	28.5	2.4	1	-3.5	0
BZT52C4V3	W6	4.09	4.3	4.52	570	85	28.5	2.4	1	-3.5	0
BZT52C4V7	W7	4.47	4.7	4.94	475	75	14	2.4	2	-3.5	0.2
BZT52C5V1	W8	4.85	5.1	5.36	455	57	14	1.6	2	-2.7	1.2
BZT52C5V6	W9	5.32	5.6	5.88	380	38	9.5	0.8	2	-2	2.5
BZT52C6V2	WA	5.89	6.2	6.51	150	9.5	5.7	2.4	4	0.4	3.7
BZT52C6V8	WB	6.46	6.8	7.14	76	14.2	5.7	1.6	4	1.2	4.5
BZT52C7V5	WC	7.13	7.5	7.88	76	14.2	5.7	0.8	5	2.5	5.3
BZT52C8V2	WD	7.79	8.2	8.61	76	14.2	5.7	0.56	5	3.2	6.2
BZT52C9V1	WE	8.65	9.1	9.56	95	14.2	7.6	0.16	7	3.8	7.0
BZT52C10	WF	9.50	10	10.50	142.5	19	9.5	0.08	8	4.5	8.0
BZT52C11	WG	10.45	11	11.55	142.5	19	9.5	0.08	8	5.4	9.0
BZT52C12	WH	11.4	12	12.60	150	23.7	9.5	0.08	8	6.0	10.0
BZT52C13	WI	12.35	13	13.65	170	28.5	14.2	0.08	8	7.0	11.0
BZT52C15	WJ	14.25	15	15.75	190	28.5	19	0.04	11	9.2	13.0
BZT52C16	WK	15.2	16	16.80	190	38	19	0.04	11	10.4	14.0
BZT52C18	WL	17.10	18	18.90	213	42.7	19	0.04	13	12.4	16.0
BZT52C20	WM	19.0	20	21.0	213	52.2	19	0.04	14	14.4	18.0
BZT52C22	WN	20.9	22	23.10	237	52.2	23.7	0.04	15	16.4	20.0
BZT52C24	WO	22.8	24	25.2	250	66.5	23.7	0.04	17	18.4	22.0

DEVICE	Marking	VZ(V) @ IZ=2mA			ZZ @ IZ = 0.5 mA	ZZ @ IZ = 2 mA	ZZ @ IZ = 10mA	IR@VR	VR	Typical Temperature Coefficient(mV/°C)@ IZ=2mA	
		MIN	NOM	MAX	(Ω)	(Ω)	(Ω)	(uA)	V	Min	Max
BZT52C27	WP	25.65	27	28.35	295	75	43	0.04	19	21.4	25.3
BZT52C30	WQ	28.50	30	31.50	295	75	48	0.04	21	24.4	29.4
BZT52C33	WR	31.35	33	34.65	320	75	53	0.04	23	27.4	33.4
BZT52C36	WS	34.20	36	37.80	345	85	58	0.04	25	30.4	37.4
BZT52C39	WT	37.05	39	40.95	345	125	68	0.04	27	33.4	41.2
BZT52C43	WU	40.85	43	45.15	370	145	78	0.04	30	37.6	46.6
BZT52C47	WV	44.65	47	49.35	370	165	88	0.04	33	42.0	51.8
BZT52C51	WW	48.45	51	53.55	395	175	98	0.04	36	46.6	57.2
BZT52C56	XW	52.2	56	58.8	420	195	108	0.04	39	52.2	63.8
BZT52C62	6E	58.9	62	65.1	445	210	118	0.04	43	58.8	71.6
BZT52C68	6F	64.6	68	71.4	470	235	128	0.04	48	65.6	79.8
BZT52C75	6H	71.25	75	78.75	495	250	138	0.04	53	73.4	88.6

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

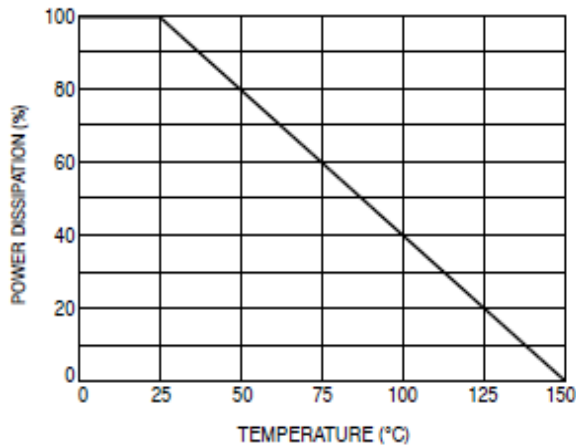


Fig.1 Power Dissipation vs Ambient Temperature

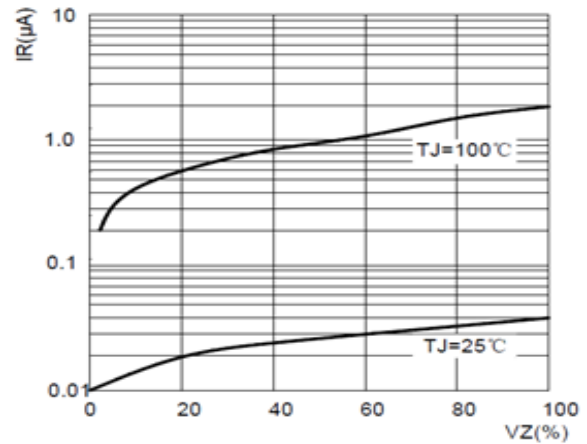


Fig.2 Typical reverse characteristics

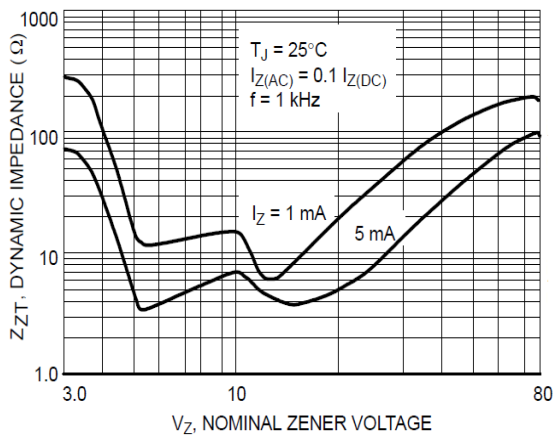


Fig.3 Characteristic curve of reverse voltage and impedance

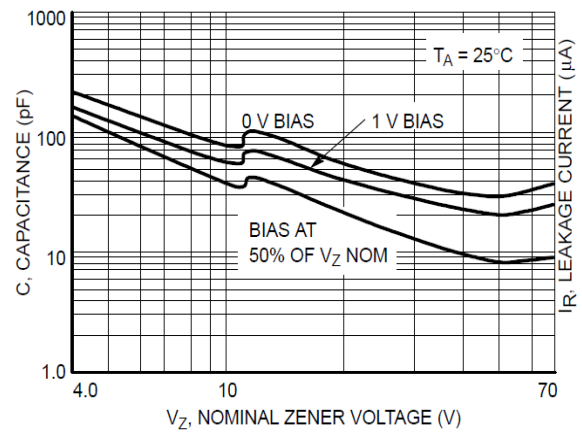
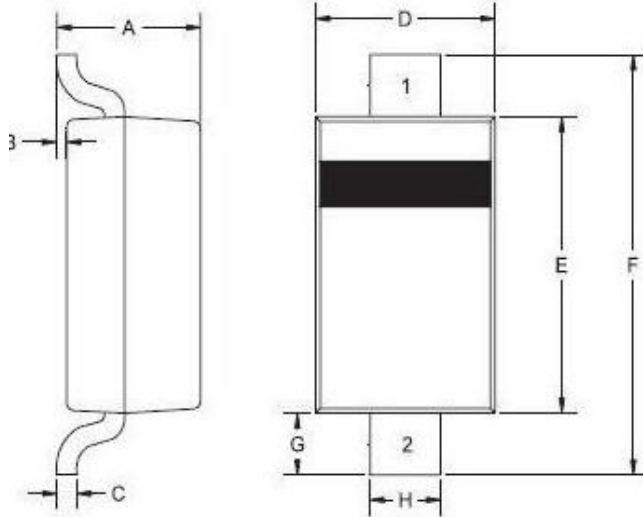


Fig.4 Typical capacitance characteristic curve

SOD-123 PACKAGE OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0,037	0,053	0,95	1,35
B	0,000	0,005	0,00	0,12
C	-	0,008	-	0,20
D	0,055	0,071	1,40	1,80
E	0,098	0,110	2,50	2,80
F	0,142	0,154	3,60	3,90
G	0,016	-	0,40	-
H	0,020	0,028	0,50	0,70

Lead Code:

PACKAGE INFORMATION

Device	Package	Shipping
BZT52C2V0-BZT52C75	SOD-123	3000/Tape&Reel